## General Description

SOP-8 P-Channel enhancement mode power field effect transistors are produced using,high cell density, DMOS technology.This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance.These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where fast switching,low in-line power loss,and resistance to transients are needed.

D	5			4	G
D	6			3	S
D	7			2	S
D	8			1	S

SOP-8
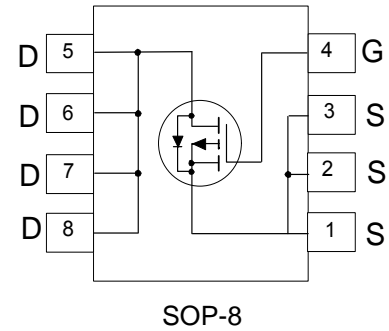
Features

- $V_{DS (V)}$ = -30V
- I_D = 7.9A (V_{GS} = 10V)
- $R_{DS(ON)} < 23m\Omega$ (V_{GS}=10V)
- $R_{DS(ON)} < 35\ m\Omega$ (V_{GS}=-4.5V)
- High density cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability in a widely used surface mount package.

Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		NDS8435A	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Drain Current - Continuous (Note 1a)		-7.9	A
	- Pulsed		-25	
P_D	Maximum Power Dissipation (Note 1a)		2.5	W
	(Note 1b)		1.2	
	(Note 1c)		1	
T_J,T_{STG}	Operating and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)		50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)		25	°C/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = -250 µA		-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -24 V, V_{GS} = 0 V				-1	µA
			T_J = 55°C			-10	µA
I_{GSSF}	Gate - Body Leakage, Forward	V_{GS} = 20 V, V_{DS} = 0 V				100	nA
I_{GSSR}	Gate - Body Leakage, Reverse	V_{GS} = -20 V, V_{DS} = 0 V				-100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 µA		-1	-1.3	-3	V
			T_J = 125°C	-0.7	-1	-2.2	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = -10 V, I_D = -7.9 A			20	23	mΩ
		V_{GS} = -4.5 V, I_D = -6.5 A			30	35	
$I_{D(on)}$	On-State Drain Current	V_{GS} = -10 V, V_{DS} = -5 V		-25			A
		V_{GS} = -4.5, V_{DS} = -5 V		-10			
g_{FS}	Forward Transconductance	V_{DS} = -10 V, I_D = -7.9 A			-17		S
C_{iss}	Input Capacitance	V_{DS} = -15 V, V_{GS} = 0 V, f = 1.0 MHz			1800		pF
C_{oss}	Output Capacitance				950		pF
C_{rss}	Reverse Transfer Capacitance				240		pF
$t_{D(on)}$	Turn - On Delay Time	V_{DD} = -10 V, I_D = -1 A, V_{GEN} = -10 V, R_{GEN} = 6 Ω			11	22	ns
t_r	Turn - On Rise Time				20	35	ns
$t_{D(off)}$	Turn - Off Delay Time				95	180	ns
t_f	Turn - Off Fall Time				46	100	ns
Q_g	Total Gate Charge	V_{DS} = -15 V, I_D = -7.9 A, V_{GS} = -10 V			48	67	nC
Q_{gs}	Gate-Source Charge				6		nC
Q_{gd}	Gate-Drain Charge				12		nC
I_S	Maximum Continuous Drain-Source Diode Forward Current					-2.1	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = -2.1 A (Note 2)			-0.74	-1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

$$P_D(t) = \frac{T_J - T_A}{R_{\theta JA(t)}} = \frac{T_J - T_A}{R_{\theta JC} + R_{\theta CA(t)}} = I_D^2(t) \times R_{DS(ON)@T_J}$$

Typical $R_{\theta JA}$ for single device operation using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

   a. 50°C/W when mounted on a 1 in^2 pad of 2oz copper.

   b. 105°C/W when mounted on a 0.04 in^2 pad of 2oz copper.

   c. 125°C/W when mounted on a 0.006 in^2 pad of 2oz copper.
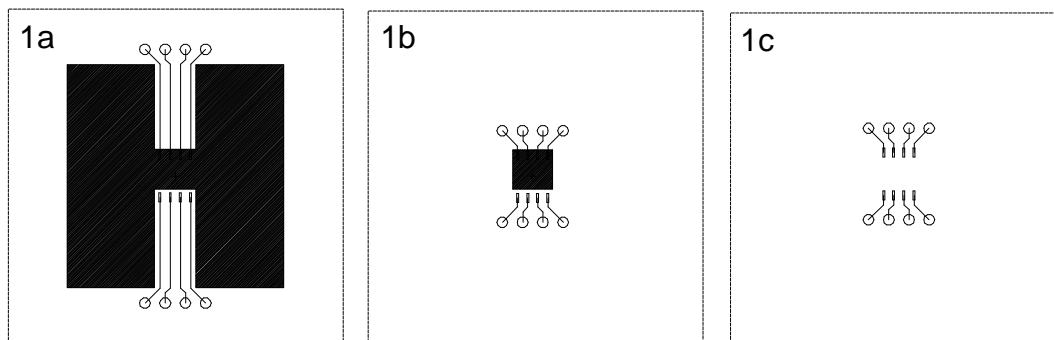
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

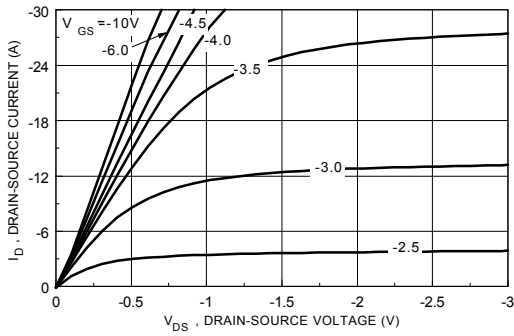**Typical Electrical Characteristics**
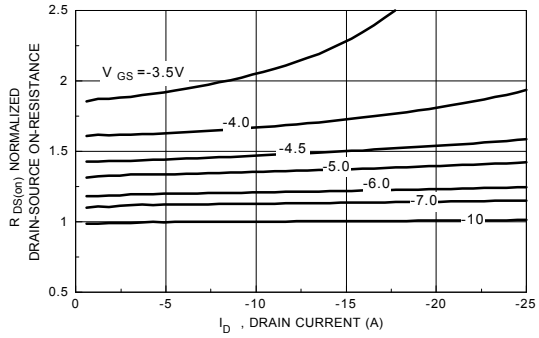

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation
with Drain Current and Gate Voltage.

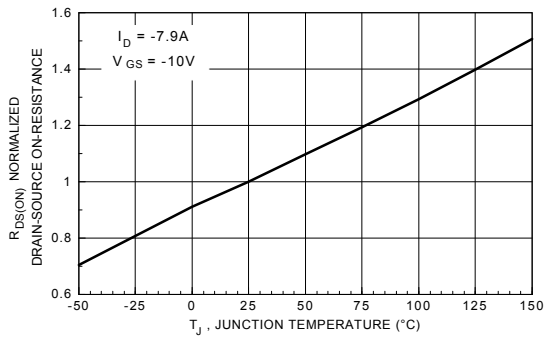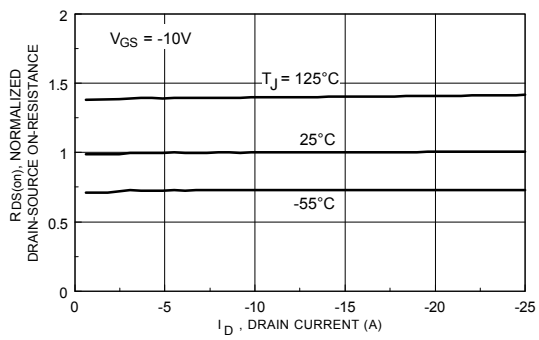

Figure 3. On-Resistance Variation
with Temperature.

Figure 4. On-Resistance Variation
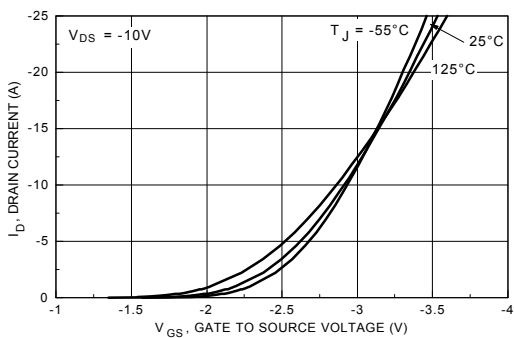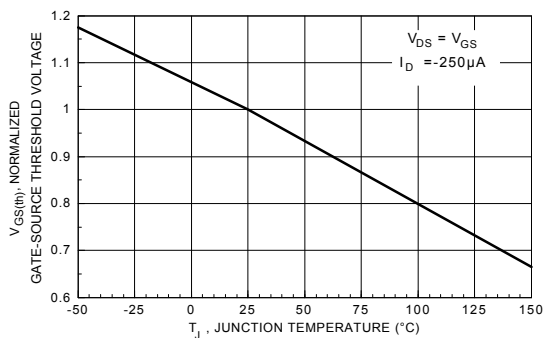with Drain Current and Temperature.

Figure 5. Transfer Charateristics.

Figure 6. Gate Threshold Variation
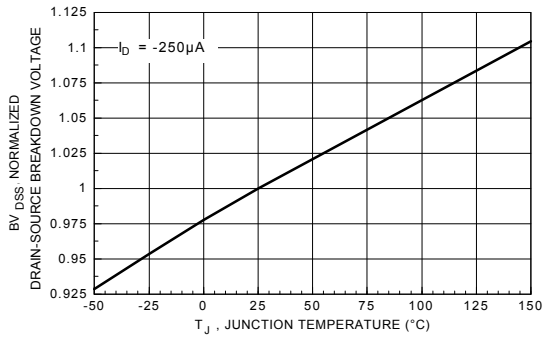with Temperature.

Typical Electrical Characteristics (continued)
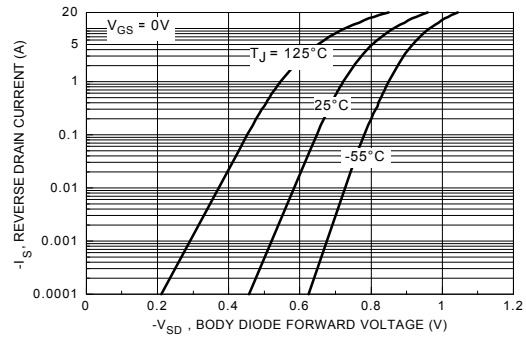

Figure 7. Breakdown Voltage Variation with Temperature.

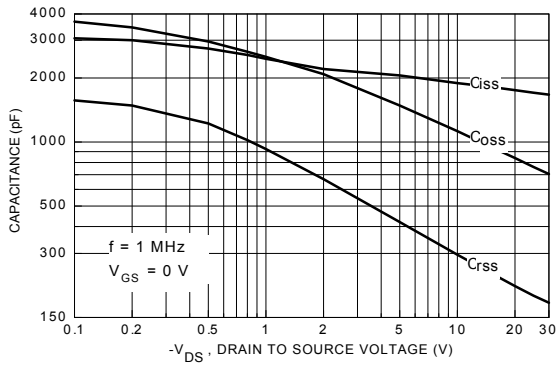**Figure 8. Body Diode Forward Voltage Variation with Source Current and Temperature.**
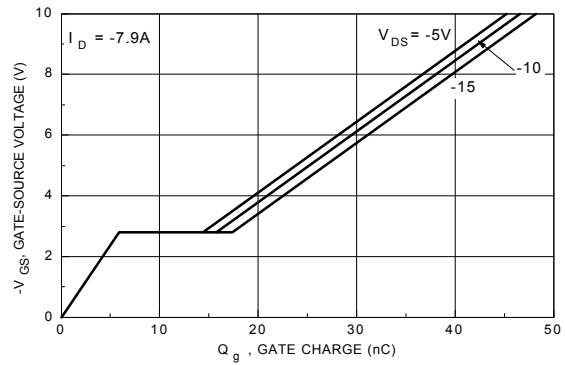

Figure 9. Capacitance Characteristics.
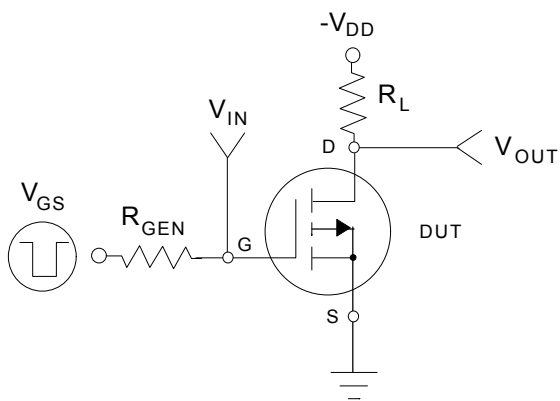

Figure 10. Gate Charge Characteristics.
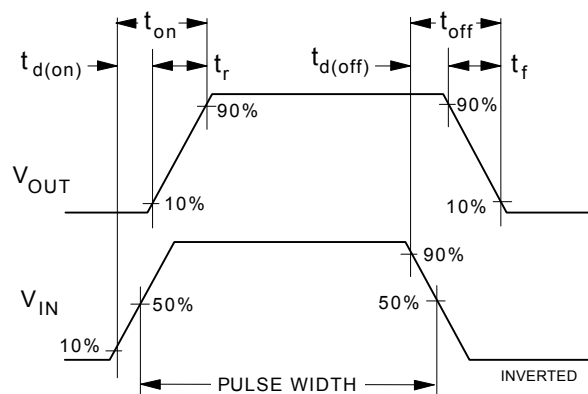

Figure 11. Switching Test Circuit.

Figure 12. Switching Waveforms.

Typical Electrical and ThermalCharacteristics (continued)
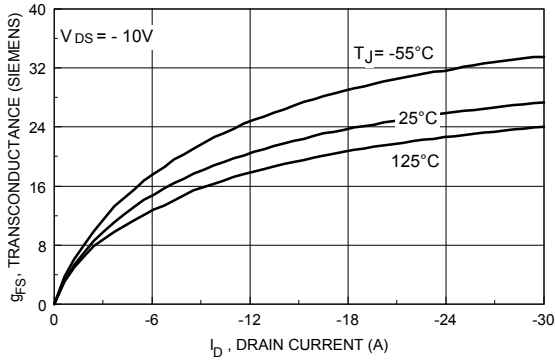

Figure 13. Transconductance Variation with Drain Current and Temperature.
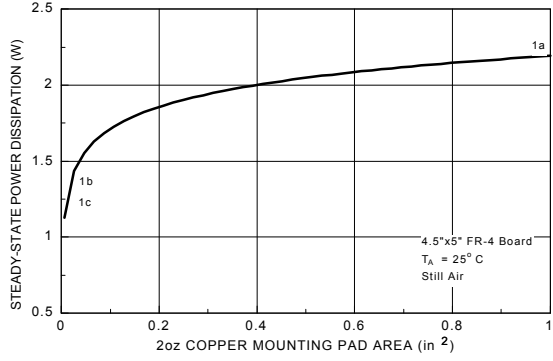

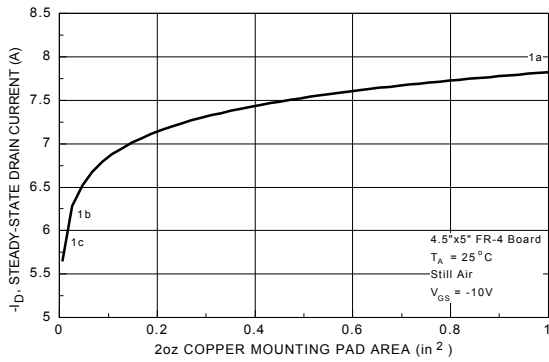Figure 14. SO-8 Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area.

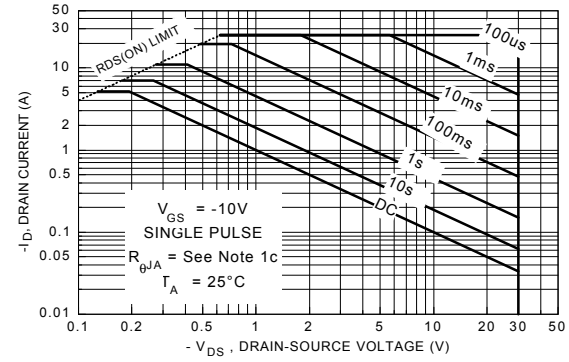Figure 15. Maximum Steady- State Drain Current versus Copper Mounting Pad Area.

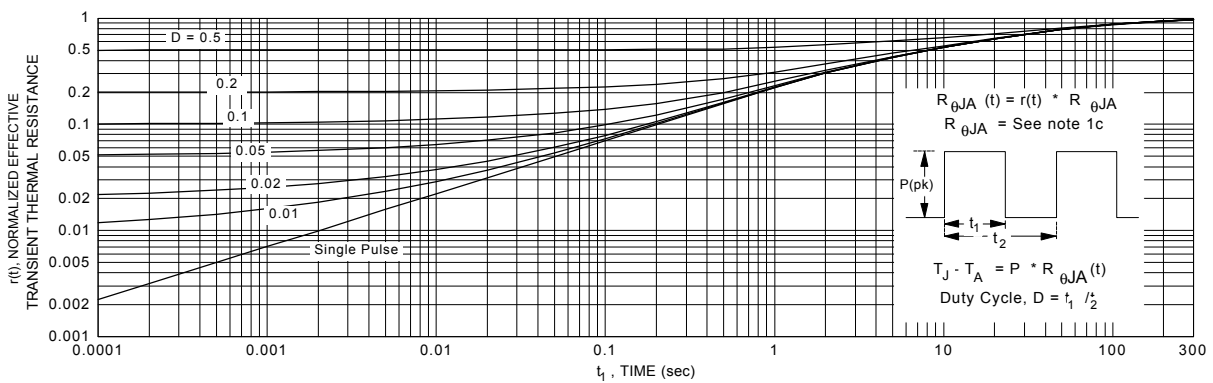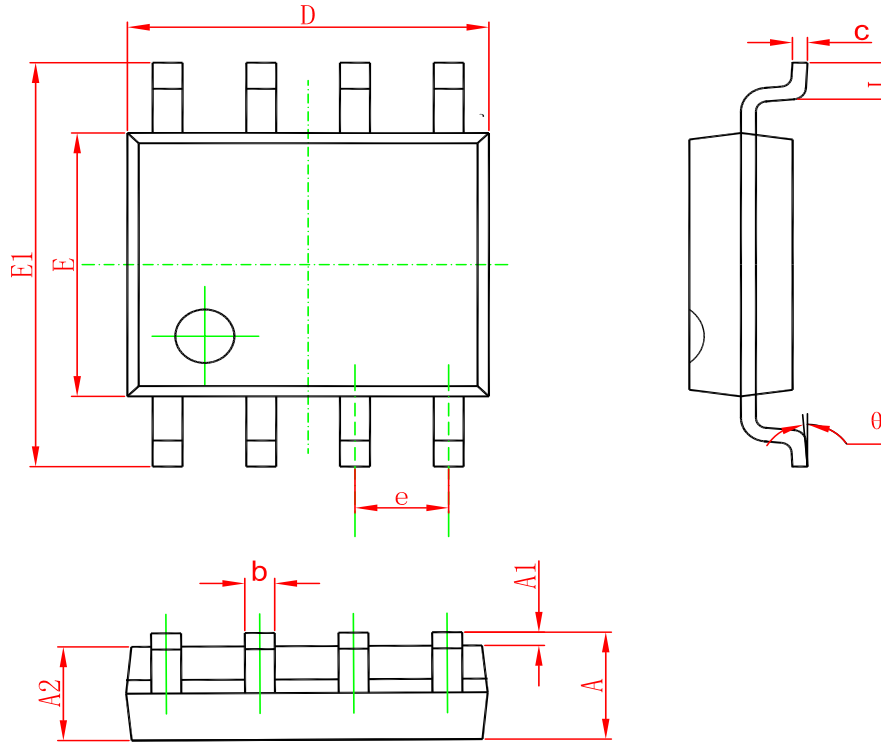Figure 16. Maximum Safe Operating Area.

Figure 17. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.
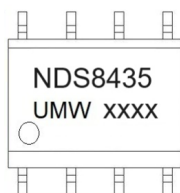
PACKAGE OUTLINE DIMENSIONS

SOP-8

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking

NDS8435
UMW xxxx

Ordering information

Order code	Package	Baseqty	Deliverymode
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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
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STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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